



General Description

The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

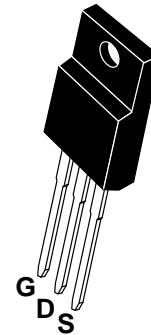
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

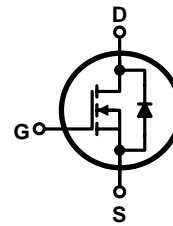
Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

PIN Connection TO-220F



Schematic diagram



Marking Diagram



- Y = Year
- A = Assembly Location
- WW = Work Week
- VT = Version & Thickness
- FIR4N80F = Specific Device Code

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-Source Voltage	800	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	3.0	A
		1.95	A
I _{DM}	Drain Current - Pulsed (Note 1)	6.0	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	180	mJ
I _{AR}	Avalanche Current (Note 1)	3.0	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	335	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	62	W
		0.50	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	2.0	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	-	120	°C/W



Electrical Characteristics

 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	800	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 640\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	--	4.0	4.8	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	290	--	pF
C_{oss}	Output Capacitance		--	30	--	pF
C_{rss}	Reverse Transfer Capacitance		--	3.5	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 2.4\text{ A},$ $R_G = 25\ \Omega$ (Note 4, 5)	--	12	35	ns
t_r	Turn-On Rise Time		--	30	70	ns
$t_{d(off)}$	Turn-Off Delay Time		--	25	60	ns
t_f	Turn-Off Fall Time		--	28	65	ns
Q_g	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 2.4\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	12	15	nC
Q_{gs}	Gate-Source Charge		--	2.6	--	nC
Q_{gd}	Gate-Drain Charge		--	6.0	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	3.0	--	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	6.0	--	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A}$	--	1.4	--	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 2.4\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	480	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.0	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 30\text{ mH}, I_{AS} = 2.0\text{ A}, V_{DD} = 80\text{ V}, R_G = 25\ \Omega,$ Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 2.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS},$ Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s},$ Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

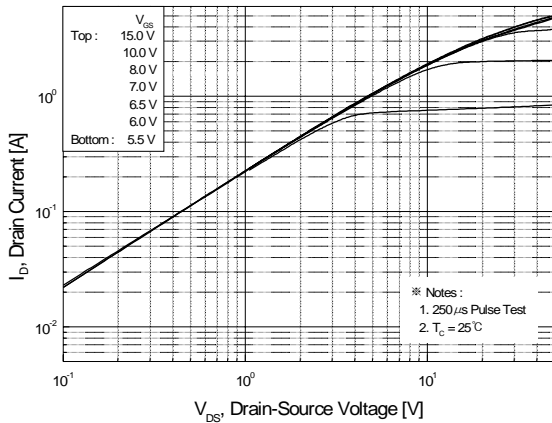


Figure 1. On-Region Characteristics

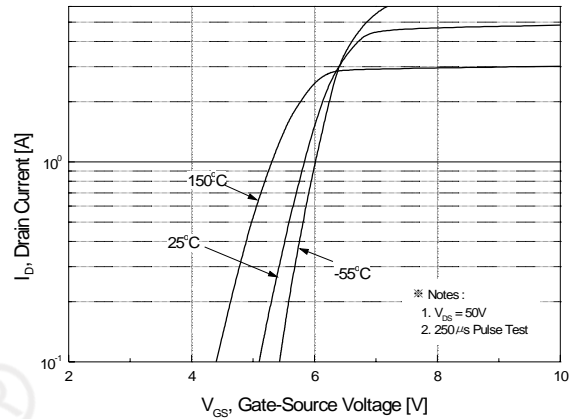


Figure 2. Transfer Characteristics

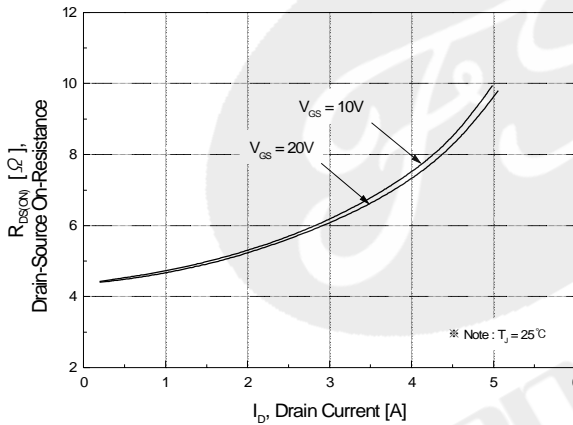


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

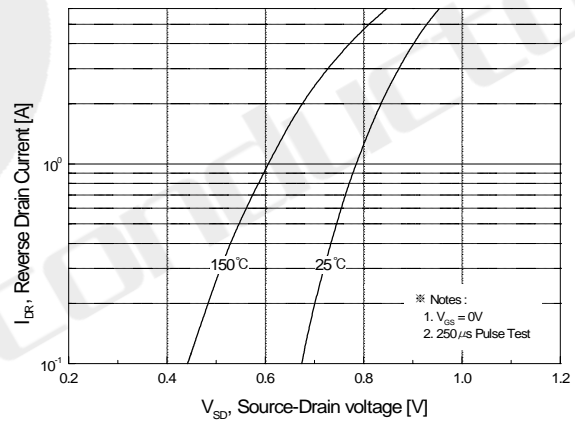


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

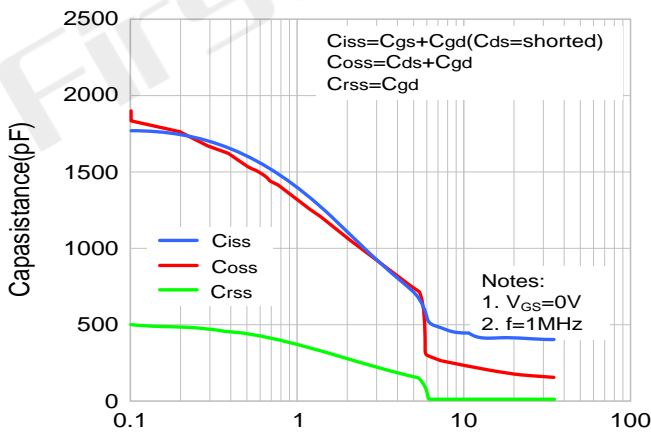


Figure 5. Capacitance Characteristics

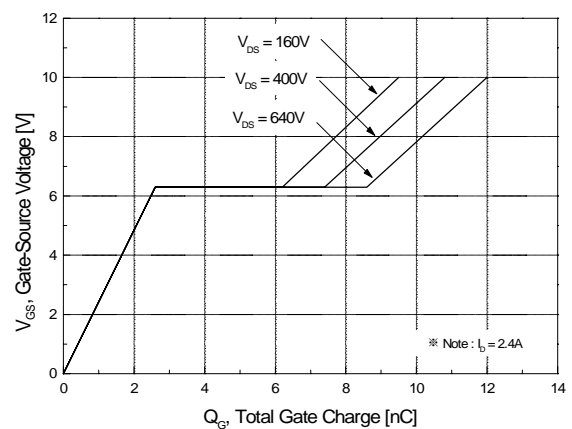


Figure 6. Gate Charge Characteristics

Typical Characteristics

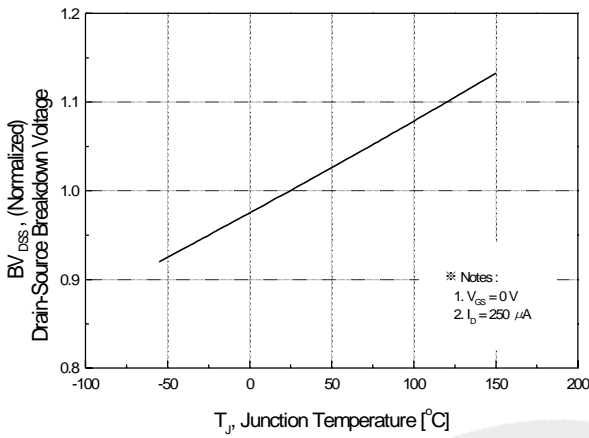


Figure 7. Breakdown Voltage Variation vs Temperature

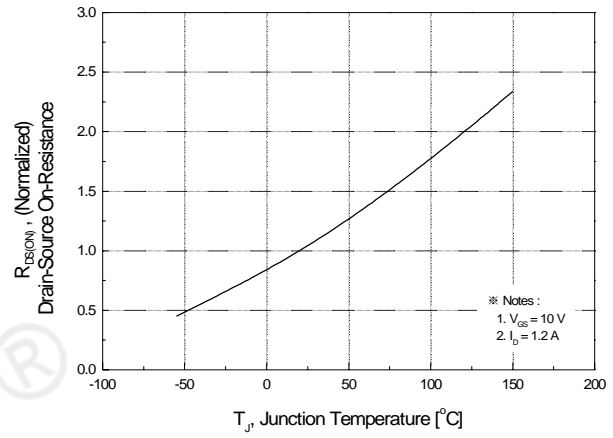


Figure 8. On-Resistance Variation vs Temperature

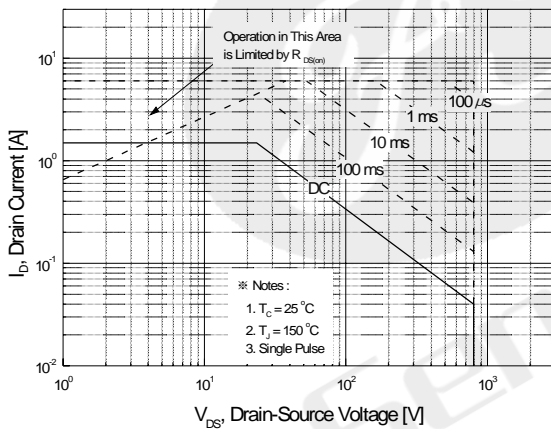


Figure 9. Maximum Safe Operating Area

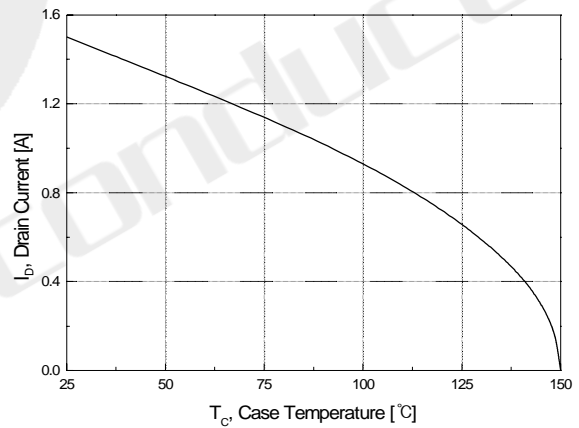


Figure 10. Maximum Drain Current vs Case Temperature

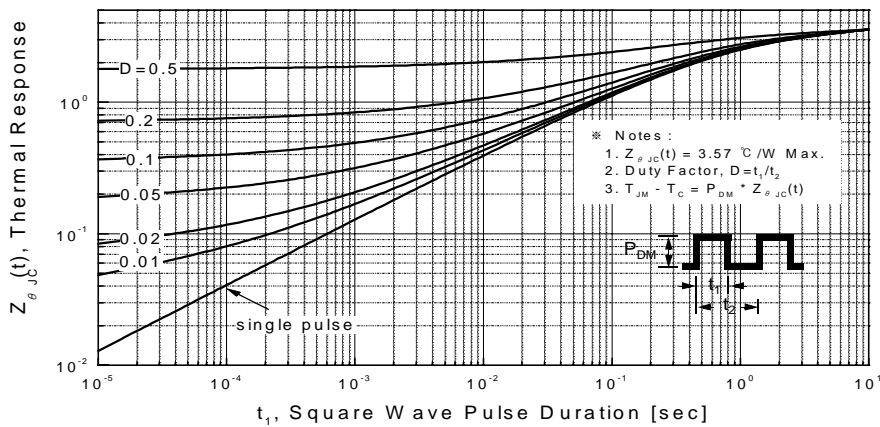
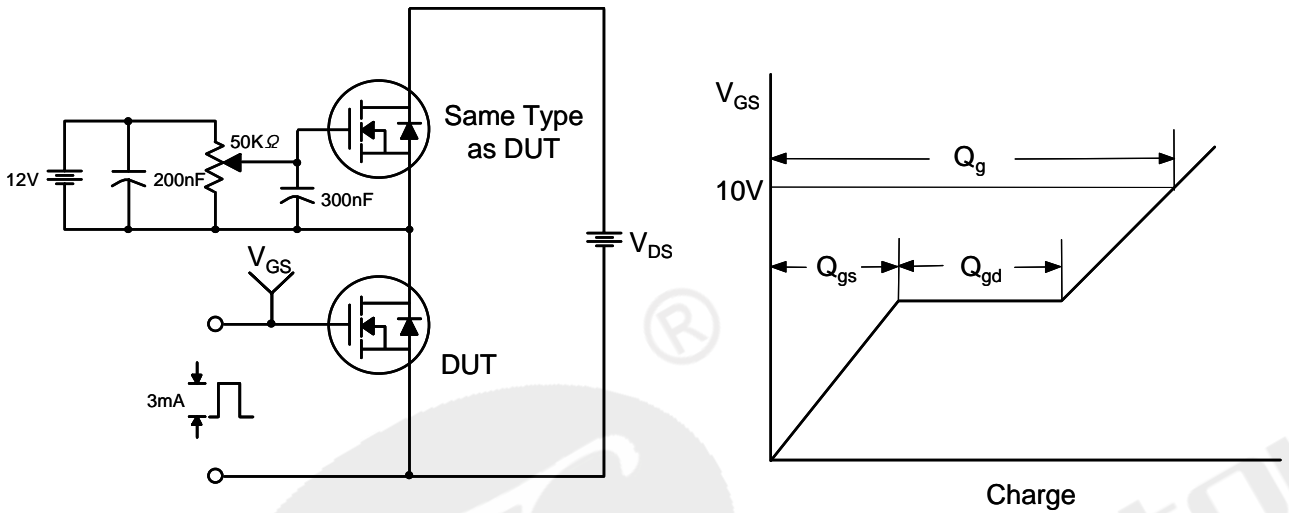
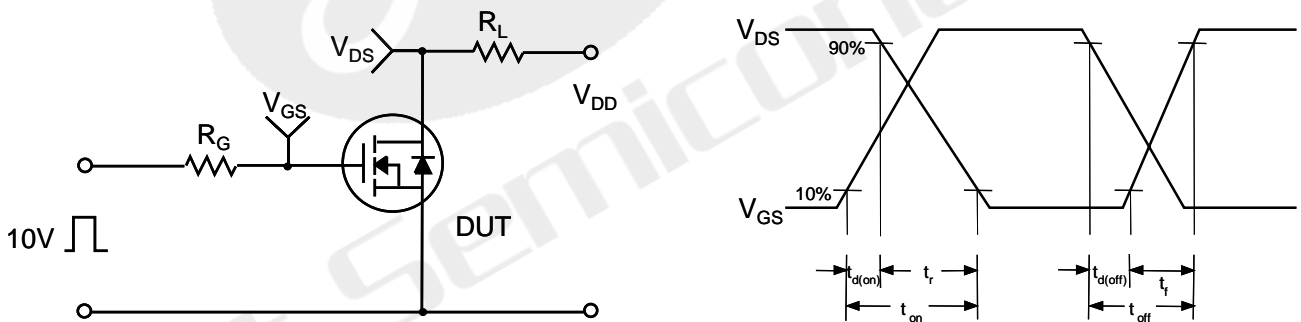


Figure 11. Transient Thermal Response Curve

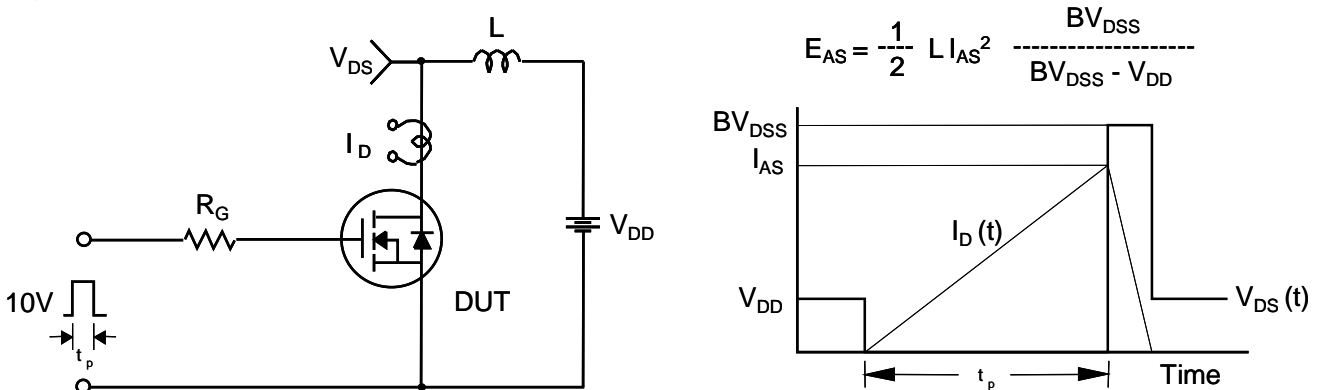
Gate Charge Test Circuit & Waveform



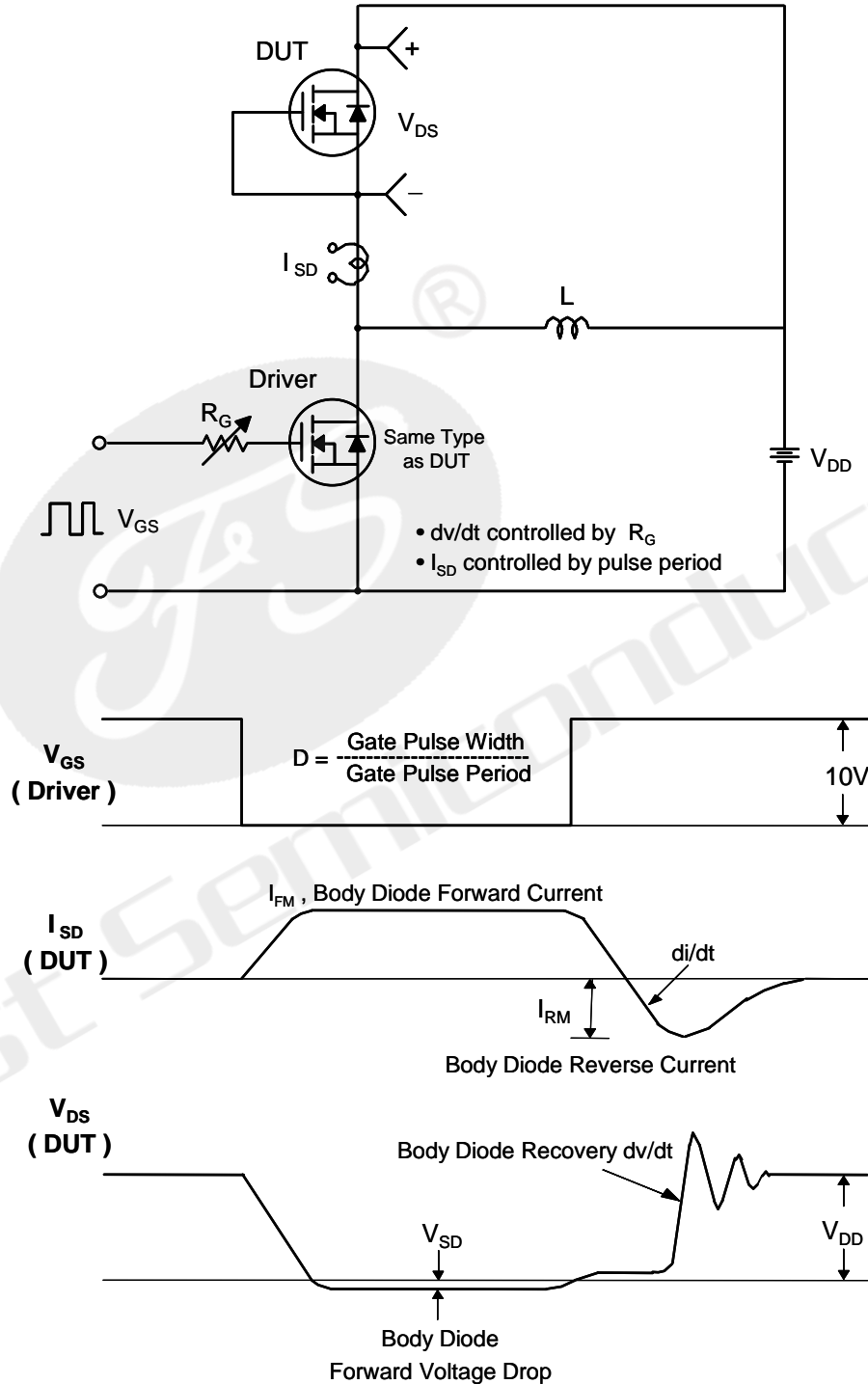
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



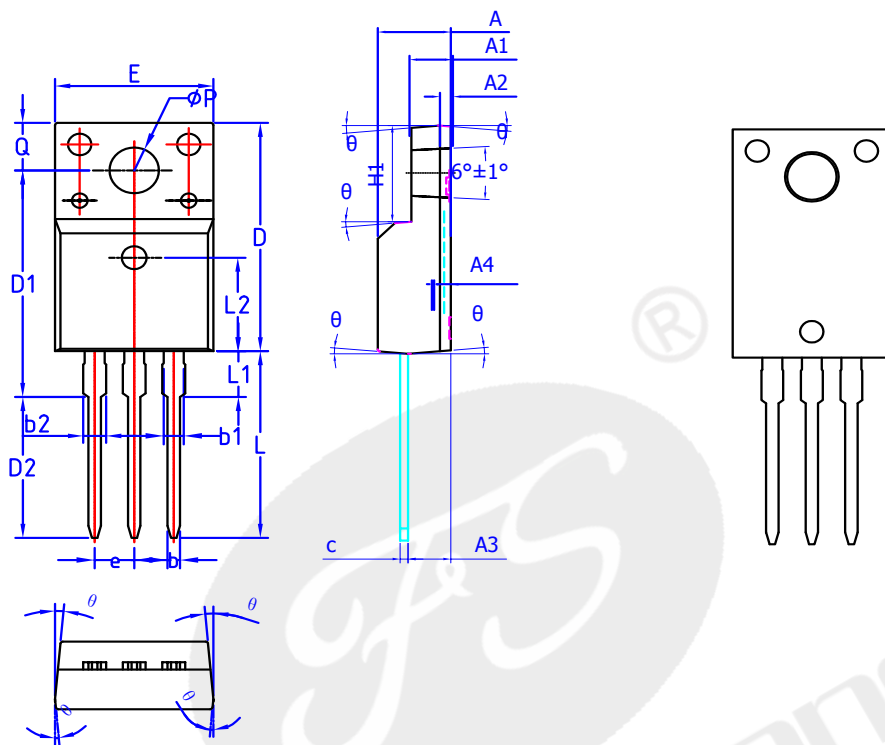
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Information

TO-220F



Units: mm
COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.96
b	0.70	0.80	0.90
b1	1.17	1.2	1.25
b2	1.17	1.2	1.25
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	10.0	10.2	10.4
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	-	-	3.50
L2	6.50REF		
φP	3.08	3.18	3.28
Q	3.20	3.30	3.40
θ 1	1°	3°	5°
A4	0.53	0.56	0.59



Declaration

- FIRST reserves the right to change the specifications, the same specifications of products due to different packaging line mold, the size of the appearance will be slightly different, shipped in kind, without notice! Customers should obtain the latest version information before ordering, and verify whether the relevant information is complete and up-to-date.
- Any semiconductor product under certain conditions has the possibility of failure or failure, The buyer has the responsibility to comply with safety standards and take safety measures when using FIRST products for system design and manufacturing, To avoid To avoid potential failure risks, which may cause personal injury or property damage!
- Product promotion endless, our company will wholeheartedly provide customers with better products!

ATTACHMENT

Revision History

Date	REV	Description	Page
2018.01.01	1.0	Initial release	